New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

Part Number: BLY93A
Description: BJTs, Si NPN Power HF

The RF Line

NPN SILICON RF POWER TRANSISTOR

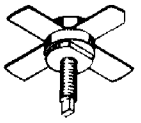
. . . designed primarily for wideband large-signal amplifier stages in the 125-175 MHz frequency range.

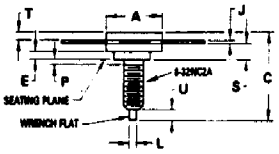
- Specified 28 Volt, 175 MHz Characteristics –
  Output Power = 40 Watts
  Minimum Gain = 7.6 dB
  Efficiency = 60%
- Characterized from 125 to 175 MHz
- Includes Series Equivalent Impedances

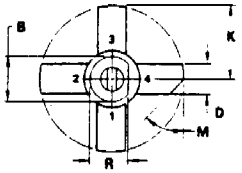
40 W – 175 MHz

RF POWER TRANSISTOR

NPN SILICON







STYLE 1:
PIN 1. EMITTER
2. BASE
3. EMITTER
4. COLLECTOR

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	9.40	9.78	0.370	0.385
B	8.13	8.38	0.320	0.330
C	17.02	20.07	0.670	0.790
D	5.46	5.97	0.215	0.235
E	1.78	—	0.070	—
J	0.08	0.18	0.003	0.007
K	12.45	—	0.490	—
L	1.40	1.78	0.055	0.070
M	45° NOM		45° NOM	
P	—	1.27	—	0.050
R	7.59	7.80	0.299	0.307
S	4.01	4.52	0.158	0.178
T	2.11	2.64	0.083	0.100
U	2.49	3.35	0.098	0.132

***MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CB}	65	Vdc
Emitter-Base Voltage	V_{EB}	4.0	Vdc
Collector Current – Continuous	I_C	5.0	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	60 342	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J,T_{stg}	-65 to +200	°C

*Indicates JEDEC Registered Data.

Quality Semi-Conductors

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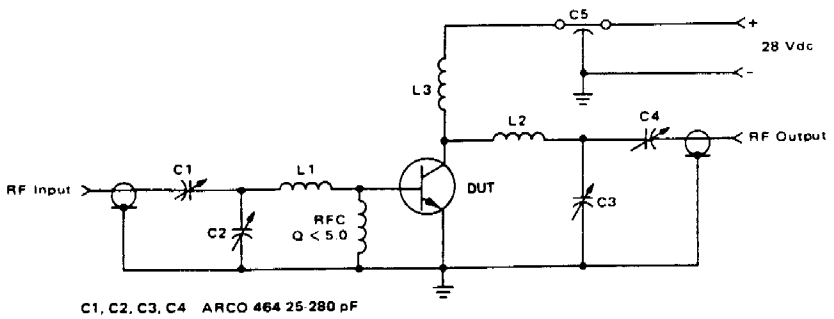
***ELECTRICAL CHARACTERISTICS** (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (Note 1) (I_C = 200 mAdc, I_B = 0)	$V_{(BR)CEO}$	35	–	–	Vdc
Collector-Emitter Breakdown Voltage (I_C = 200 mAdc, V_{BE} = 0)	$V_{(BR)CES}$	65	–	–	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 mAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	–	–	1.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 500 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	5.0	–	–	–
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 30 Vdc, I_E = 0, f = 0.1 to 1.0 MHz)	C_{ob}	–	45	65	pF
FUNCTIONAL TEST					
Common-Emitter Amplifier Power Gain (Figure 1) (P_{out} = 40 Watts, V_{CE} = 28 Vdc, f = 175 MHz)	G_{PE}	7.6	8.1	–	dB
Collector Efficiency (Figure 1) (P_{out} = 40 Watts, V_{CE} = 28 Vdc, f = 175 MHz)	η	60	–	–	%

Note 1: Pulsed through 25 mH inductor.
*Indicates JEDEC Registered Data.

FIGURE 1 – 175 MHz TEST CIRCUIT SCHEMATIC



C1, C2, C3, C4	ARCO 464 25-280 pF
C5	0.1 μF
L1	1" Straight #14 AWG
L2	1 Turn #16 AWG, 1/4" I.D.
L3	0.22 μH